

IN THE CLAIMS:

Please cancel claims 15-16, 19-20, and 24-28, and amend the claims as follows:

1-13 (Cancelled)

14. (Currently Amended) A method of forming a contact ring, comprising:

providing ~~[[a]]~~ an annular substrate;

depositing at least a ~~first one~~ one conductive layer on the annular substrate, wherein said ~~first~~ conductive layer coats ~~a~~ all support surface~~[[s]]~~ of the annular substrate; ~~[[and]]~~

depositing at least a ~~first one~~ one insulative layer adjacent to the ~~at least a first~~ conductive layer, on the annular substrate, wherein said ~~first~~ insulative layer coats all surfaces of the ~~substrate~~ conductive layer; and

electrically connecting a contact to the conductive layer through said insulative layer on the annular substrate.

15-16. (Cancelled)

17. (Currently Amended) The method of claim 14 ~~[[16]]~~, further comprising ~~electrically connecting a contact to at least one of the conductive layers, wherein the~~ depositing a compliant ridge extends around the periphery of that surrounds the contact.

18. (Currently Amended) A contact ring for providing electrical contact between a wafer and a power supply, comprising:

a conductive layer positioned on at least one support surface of an annular substrate;

an insulative layer deposited above the conductive layer;

a contact in electrical contact with the conductive layer and extending through the insulative layer above the conductive layer to an external surface; and

a compliant ridge formed on the external surface, and extending about the periphery of the contact.

Jan-16-04 07:55pm From-Moser, Patterson & Sheridan L.L.P.

+713 623 4846

T-615 P.004/006 F-818

PATENT
Atty. Dkt. No. AMAT/3482.D1/CMP/ECP/RKK

19-28. (Cancelled)

Page 3

C:\NRPORTBL\IMANAGE\KMTACKETT\247237_1.DOC

PAGE 4/6 * RCVD AT 1/16/2004 7:50:33 PM [Eastern Standard Time] * SVR:USPTO-EFXXRF-1/2 * DNIS:8729306 * CSID:+7136234846 * DURATION (mm-ss):01-20